

Abstract

The present invention provides a method of fabricating a capacitor for improving the shape of a bottom electrode by 5 using a sacrificial layer at a producing process. For this object, the method for fabricating the capacitor for a semiconductor device includes the step of: forming a sacrificial layer in the height of capacitor on the substrate so that a etch rate becomes lower if it's height becomes 10 higher; forming a trench by selectively eliminating the sacrifice layer in manner of wet etch process; forming a bottom electrode in the trench; eliminating the sacrificial layer; forming a dielectric thin film on the bottom electrode; and forming the top electrode on the dielectric thin film.

15